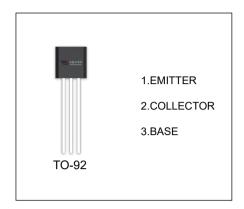


2SC1008 TRANSISTOR (NPN)

FEATURES

General Purpose Switching and Amplification



ORDERING INFORMATION®

Part Number	Package	Packing Method		Pack Quantity
2SC1008	TO-92	Bulk		1000pcs/Bag
2SC1008-TA	TO-92	Таре	G	2000pcs/Box

MAXIMUM RATINGS (T_a =25 $^{\circ}$ C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	8	V
Ic	Collector Current	700	mA
Pc	Collector Power Dissipation	800	mW
R _{θ JA}	Thermal Resistance From Junction To Ambient	156	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.1mA,I _E =0	80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA,I _B =0	60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.01mA,I _C =0	8			V
Collector cut-off current	I _{CBO}	V _{CB} =60V,I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V,I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =2V, I _C =50mA	40		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500mA,I _B =50mA			0.4	V
Base-emitter saturation voltage	V _{BE (sat)}	I _C =500mA,I _B =50mA			1.1	V
Collector output capacitance	C _{ob}	V _{CB} =10V,I _C =0, f=1MHz		8		pF
Transition frequency	f _T	VcE=10V,Ic= 50mA	30			MHz

CLASSIFICATION OF h_{FE}

RANK	R	0	Υ	G	
RANGE	40-80	70-140	120-240	200-400	



